

MG031MC148004A

MOSFET Array

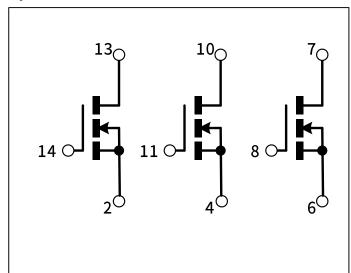
Feature

- MOSFET Array
- MOSFET(N-channel)
- High current capacity
- Low Ron
- Halogen free
- Pb free terminal
- RoHS:Yes

Outline



Equivalent circuit



Absolute maximum ratings ($Tc = 25^{\circ}C$ unless otherwise specified)

MOSFET

Item	Symbol	Conditions	Ratings	Unit
Channel temperature	Tch		175	°C
Drain-source voltage	V_{DSS}		40	V
Gate-source voltage	V_{GSS}		±20	V
Continuous drain current (DC)	I _D		148	А
Continuous drain current (Peak)	I _{DP}	Pulse width 10μs, Duty = 1/100	592	А
Total power dissipation	P _T		154	W
Single avalanche current	I _{AS}	Starting Tch=25°C Tch≦150°C	51	А
Single avalanche energy	E _{AS}	Starting Tch=25°C Tch≦150°C	289	mJ

Module

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55~150	°C
Mounting torque	TOR	Fixing screw M3	0.8	N · m

These are characteristics of the 1 chip unless otherwise specified.

MOSFET

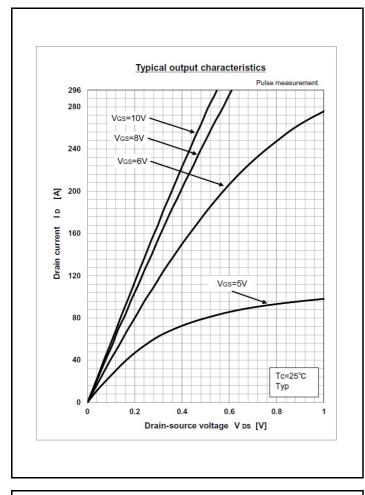
Item	Symbol	Conditions	Ratings			Unit	
		Conditions		Min.	Тур.	Max.	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0V		40	_	_	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =40V, V _{GS} =0V		_	_	1.0	μΑ
Gate-source leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V		_	_	±0.1	μΑ
Static drain-source on-state resistance	_	Chip	I _D =74A, V _{GS} =10V	_	1.25	_	mΩ
	R _{DS(ON)}	Terminal	I _D =74A, V _{GS} =10V	_	1.75	2.20	mΩ
Gate threshold voltage	V_{TH}	I _D =1mA, V _{DS} =10V		2.0	3.0	4.0	V
Source-drain diode forward voltage	V _{SD}	Is=148A, V _{GS} =0V		_	_	1.5	V
Total gate charge	Qg	V_{DD} =32V, V_{GS} =10V, I_{D} =148A (Electrical characteristics of discrete MOSFET device)		_	96	-	nC
Gate to source charge	Qgs			_	27	_	
Gate to drain charge	Qgd			_	33	_	
Input capacitance	Ciss	I _D =1mA, V _{DS} =10V Is=148A, V _{GS} =0V V _{DD} =32V, V _{GS} =10V, I _D =148A		_	5330	_	pF
Reverse transfer capacitance	Crss			_	390	_	
Output capacitance	Coss			_	833	_	
Turn-on delay time	td(on)			_	590	_	
Rise time	tr		_	620	_	- ns	
Turn-off delay time	td(off)			_	2310		_
Fall time	tf			_	510		_
Source-drain diode reverse recovery time	trr	-IF=148A, VGS=0V, di/dt=100A/μs		_	26	_	ns
Source-drain diode reverse recovery charge	Qrr			_	14	_	nC

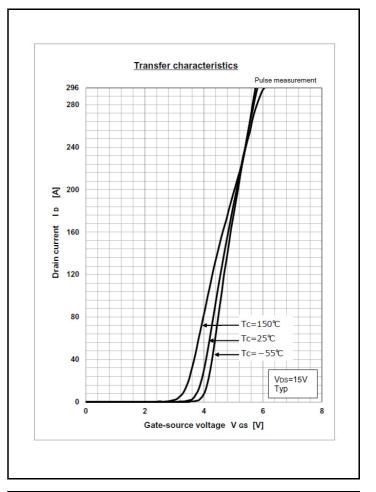
Module

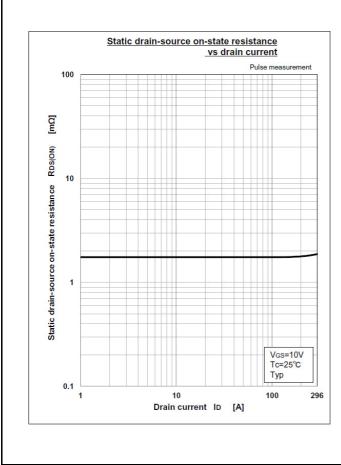
Item	Symbol	Conditions	Ratings			Unit	
			Min.	Тур.	Max.		
Thermal resistance	$R_{th(j-c)}$	Junction to case	_	1	0.97		
		Junction to lead	_	1	1.41		
	$R_{th(j-l)}$	Junction to lead, With insulating sheet, Thickness 0.3mm, Thermal conductivity 3.9W/mK	_	_	2.16	°C/W	

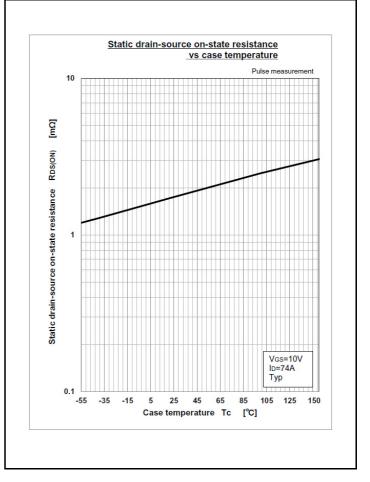
Note: Thermal resistance was measured at Q1

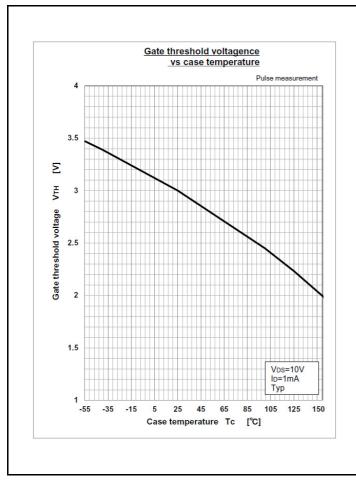
CHARACTERISTIC DIAGRAMS

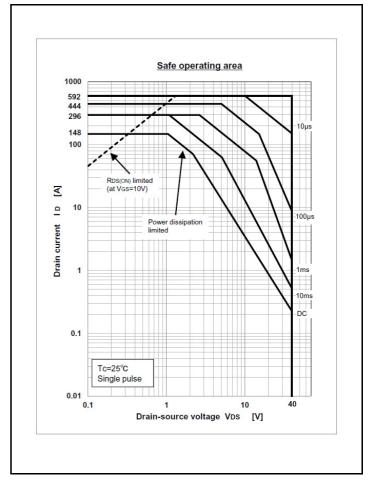


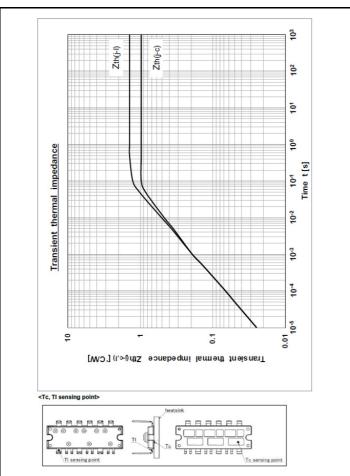


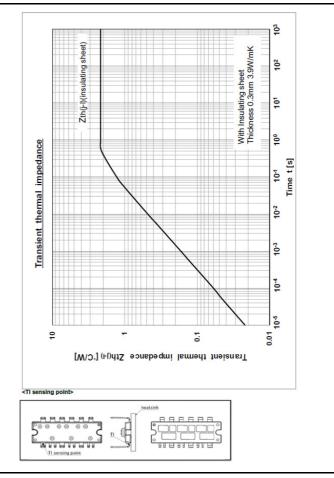


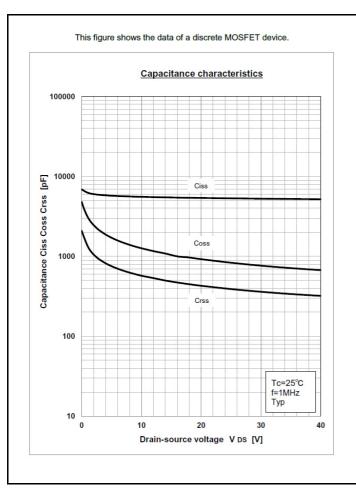


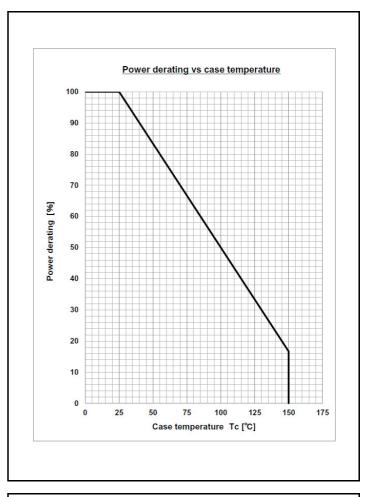


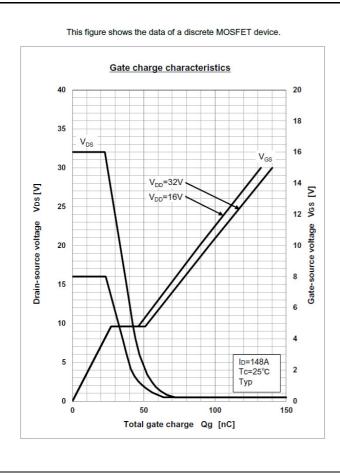


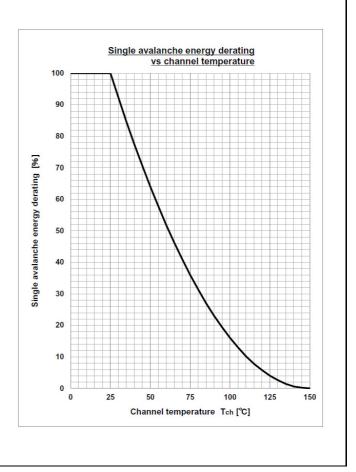








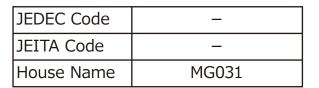


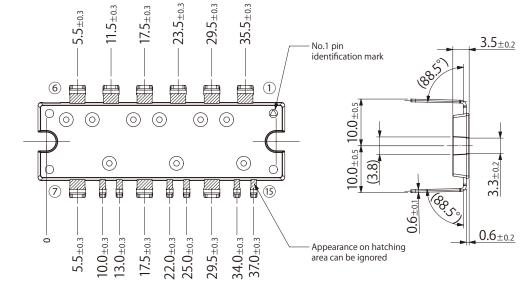


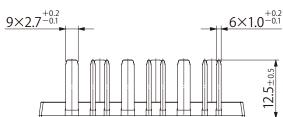
Package Outline-Dimensions

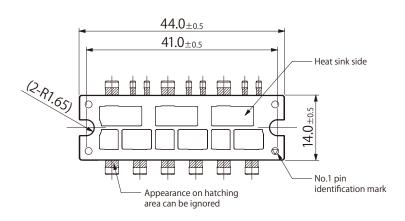
unit:mm

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